Silicon PNP Power Transistors 2SA957 2SA958

DESCRIPTION

- With TO-220 package
- High breakdown voltage
- High power dissipation

APPLICATIONS

- For general purpose applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

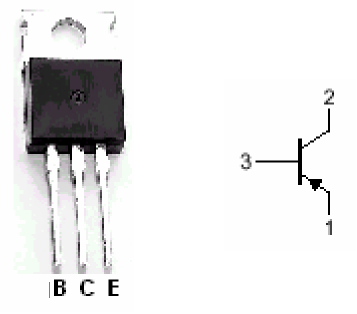

Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SA957	Open emitter	-150	V
		2SA958		-200	
V_{CEO}	Collector-emitter voltage	2SA957	Open base	-150	V
		2SA958		-200	
V_{EBO}	Emitter-base voltage		Open collector	-6	V
I_C	Collector current			-2.0	A
I_B	Base current			-1.0	A
P_T	Total power dissipation		T_C=25℃	30	W
T_j	Junction temperature			150	℃
T_{stg}	Storage temperature			-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(BR)}$	Collector-emitter breakdown voltage	2SA957	I_C=-25mA ,I_B=0	-150			V
		2SA958		-200			
V_{CEsat}	Collector-emitter saturation voltage		I_C=-0.7A; I_B=-0.07A			-1.5	V
I_{CBO}	Collector cut-off current	2SA957	V_{CB}=-150V; I_E=0			-100	μA
		2SA958	V_{CB}=-200V; I_E=0				
I_{EBO}	Emitter cut-off current		V_{EB}=-6V; I_C=0			-1.0	mA
h_{FE}	DC current gain		I_C=-0.7A ; V_{CE}=-10V	40			
f_T	Transition frequency		I_C=-0.2A ; V_{CE}=-12V		20		MHz

Switching times resistive load

t_r	Rise time	I_C=-1.0A I_{B1}=- I_{B2}=-0.1A R_L=20Ω;V_{CC}=-20V		0.4		μs
t_s	Storage time			1.5		μs
t_f	Fall time			0.5		μs

PACKAGE OUTLINE

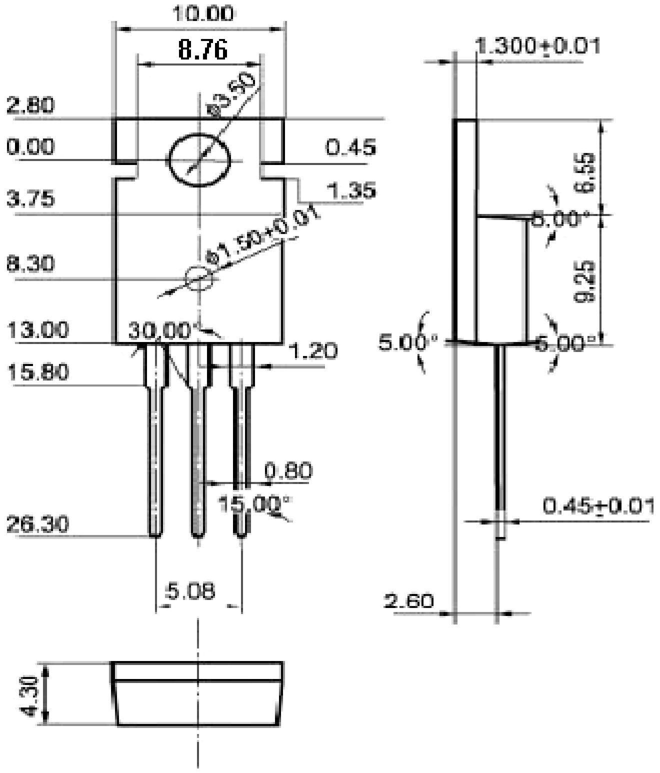

Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)